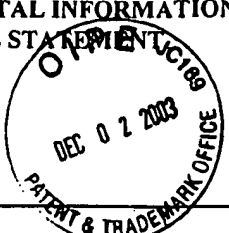
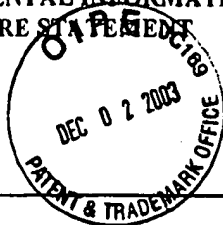


FORM PTO - 1449				ATTY DOCKET NO.: ASC-023DVC2			
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Fitzgerald			
				SERIAL NO.: 10/022,689			
				FILING DATE: December 17, 2001			
				GROUP: 2813			
<b>U.S. PATENT DOCUMENTS</b>							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>LL</i>	A1	4,010,045	03/01/1977	Ruehrwein			
<i>LL</i>	A2	4,710,788	12/01/1987	Dambkes et al.			
<i>LL</i>	A3	4,987,462	01/22/1991	Kim et al.			
<i>LL</i>	A4	4,990,979	02/05/1991	Otto			
<i>LL</i>	A5	5,013,681	05/07/1991	Godbey et al.			
<i>LL</i>	A6	5,155,571	10/13/1992	Wang et al.			
<i>LL</i>	A7	5,166,084	11/24/1992	Pfiester			
<i>LL</i>	A8	5,202,284	04/01/1993	Kamins et al.			
<i>LL</i>	A9	5,207,864	05/04/1993	Bhat et al.			
<i>LL</i>	A10	5,208,182	05/04/1993	Narayan et al.			
<i>LL</i>	A11	5,212,110	05/18/1993	Pfiester et al.			
<i>LL</i>	A12	5,221,413	06/22/1993	Brasen et al.			
<i>LL</i>	A13	5,241,197	08/31/1993	Murakami et al.			
<i>LL</i>	A14	5,285,086	02/08/1994	Fitzgerald, Jr.			
<i>LL</i>	A15	5,291,439	03/01/1994	Kauffmann, et al.			
<i>LL</i>	A16	5,310,451	05/10/1994	Tejwani et al.			
<i>LL</i>	A17	5,316,958	05/31/1994	Meyerson			
<i>LL</i>	A18	5,346,848	09/13/1994	Gruppen-Shemansky et al.			
<i>LL</i>	A19	5,374,564	12/20/1994	Bruel			
<i>LL</i>	A20	5,413,679	05/09/1995	Godbey			
<i>LL</i>	A21	5,426,069	06/20/1995	Selvakumar et al.			
<i>LL</i>	A22	5,426,316	06/20/1995	Mohammad			
<i>LL</i>	A23	5,461,243	10/24/1995	Ek et al.			
<i>LL</i>	A24	5,461,250	10/24/1995	Burghartz et al.			
<i>LL</i>	A25	5,462,883	10/31/1995	Dennard et al.			
<i>LL</i>	A26	5,476,813	12/19/1995	Naruse			
<i>LL</i>	A27	5,479,033	12/26/1995	Baca et al.			
<i>LL</i>	A28	5,484,664	01/16/1996	Kitahara et al.			
<i>LL</i>	A29	5,523,243	06/04/1996	Mohammad			
<i>LL</i>	A30	5,523,592	06/04/1996	Nakagawa et al.			
EXAMINER <i>Wesley Schults</i>				DATE CONSIDERED <i>8/4/04</i>			

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<b>FORM PTO - 1449</b>  <b>SUPPLEMENTAL INFORMATION</b> <b>DISCLOSURE STATEMENT</b>	<b>ATTY DOCKET NO.:</b> ASC-023DVC2  <b>APPLICANTS:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/022,689  <b>FILING DATE:</b> December 17, 2001  <b>GROUP:</b> 2813
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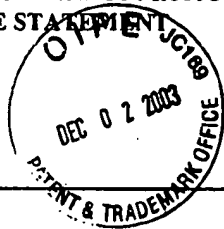
## U.S. PATENT DOCUMENTS

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X	A31	5,536,361	07/16/1996	Kondo et al.			
X	A32	5,540,785	07/30/1996	Dennard et al.			
X	A33	5,596,527	01/12/1997	Tomioka, et al.			
X	A34	5,617,351	04/01/1997	Bertin, et al.			
X	A35	5,683,934	11/04/1997	Candelaria			
X	A36	5,698,869	12/16/1997	Yoshimi et al.			
X	A37	5,728,623	03/17/1998	Mori			
X	A38	5,739,567	04/14/1998	Wong			
X	A39	5,759,898	06/02/1998	Ek et al.			
X	A40	5,777,347	07/07/1998	Bartelink			
X	A41	5,786,612	07/28/1998	Otani et al.			
X	A42	5,786,614	07/28/1998	Chuang, et al.			
X	A43	5,792,679	08/11/1998	Nakato			
X	A44	5,808,344	09/15/1998	Ismail et al.			
X	A45	5,847,419	12/08/1998	Imai et al.			
X	A46	5,877,070	03/02/1999	Goesele et al.			
X	A47	5,906,708	05/25/1999	Robinson et al.			
X	A48	5,912,479	06/15/1999	Mori et al.			
X	A49	5,943,560	08/24/1999	Chang et al.			
X	A50	5,963,817	10/05/1999	Chu et al.			
X	A51	5,966,622	10/12/1999	Levine et al.			
X	A52	5,998,807	12/07/1999	Lustig et al.			
X	A53	6,013,134	01/11/2000	Chu et al.			
X	A54	6,033,974	03/07/2000	Henley et al.			
X	A55	6,033,995	03/07/2000	Muller			
X	A56	6,058,044	05/02/2000	Sugiura et al.			
X	A57	6,074,919	06/13/2000	Gardner et al.			
X	A58	6,096,590	08/01/2000	Chan et al.			
X	A59	6,103,559	08/15/2000	Gardner et al.			
X	A60	6,111,267	08/29/2000	Fischer et al.			

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EXAMINER <i>Wesley Schult</i>	DATE CONSIDERED <i>8/4/04</i>
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FORM PTO - 1449

SUPPLEMENTAL INFORMATION  
DISCLOSURE STATEMENT

ATTY DOCKET NO.: ASC-023DVC2

APPLICANTS: Fitzgerald

SERIAL NO.: 10/022,689

FILING DATE: December 17, 2001

GROUP: 2813

## U.S. PATENT DOCUMENTS

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<i>Pl</i>	A61	6,117,750	09/12/2000	Bensahel et al.			
<i>Pl</i>	A62	6,130,453	10/10/2000	Mei, et al.			
<i>Pl</i>	A63	6,133,799	10/17/2000	Favors, Jr., et al.			
<i>Pl</i>	A64	6,140,687	10/31/2000	Shimomura et al.			
<i>Pl</i>	A65	6,143,636	11/07/2000	Forbes, et al.			
<i>Pl</i>	A66	6,153,495	11/28/2000	Kub et al.			
<i>Pl</i>	A67	6,154,475	11/28/2000	Soref et al.			
<i>Pl</i>	A68	6,160,303	12/12/2000	Fattaruso			
<i>Pl</i>	A69	6,162,688	12/19/2000	Gardner et al.			
<i>Pl</i>	A70	6,184,111	02/06/2001	Henley et al.			
<i>Pl</i>	A71	6,191,007	02/20/2001	Matsui et al.			
<i>Pl</i>	A72	6,191,432	02/20/2001	Sugiyama et al.			
<i>Pl</i>	A73	6,194,722	02/27/2001	Fiorini et al.			
<i>Pl</i>	A74	6,204,529	03/20/2001	Lung, et al.			
<i>Pl</i>	A75	6,207,977	03/01/2001	Augusto			
<i>Pl</i>	A76	6,210,988	04/03/2001	Howe et al.			
<i>Pl</i>	A77	6,218,677	04/17/2001	Broekaert			
<i>Pl</i>	A78	6,232,138	05/15/2001	Fitzgerald et al.			
<i>Pl</i>	A79	6,235,567	05/22/2001	Huang			
<i>Pl</i>	A80	6,242,324	06/05/2001	Kub et al.			
<i>Pl</i>	A81	6,249,022	06/19/2001	Lin, et al.			
<i>Pl</i>	A82	6,251,755	06/26/2001	Furukawa et al.			
<i>Pl</i>	A83	6,261,929	07/01/2001	Gehrke et al.			
<i>Pl</i>	A84	6,266,278	07/24/2001	Harari, et al.			
<i>Pl</i>	A85	6,271,551	08/07/2001	Schmitz et al.			
<i>Pl</i>	A86	6,271,726	08/07/2001	Fransis et al.			
<i>Pl</i>	A87	6,313,016	11/06/2001	Kibbel et al.			
<i>Pl</i>	A88	6,316,301	11/13/2001	Kant			
<i>Pl</i>	A89	6,323,108	11/27/2001	Kub et al.			
<i>Pl</i>	A90	6,329,063	12/11/2001	Lo et al.			

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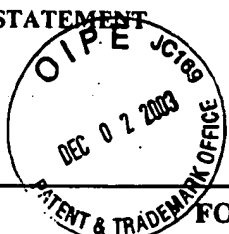
*Wesley Schuyt*

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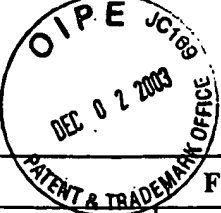
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FORM PTO - 1449				ATTY DOCKET NO.: ASC-023DVC2			
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Fitzgerald			
				SERIAL NO.: 10/022,689			
				FILING DATE: December 17, 2001			
				GROUP: 2813			
 <b>U.S. PATENT DOCUMENTS</b>							
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<i>RL</i>	A91	6,335,546	01/01/2002	Tsuda et al.			07/30/1999
<i>RL</i>	A92	6,339,232	01/15/2002	Takagi			09/20/1999
<i>RL</i>	A93	6,368,733	04/09/2002	Nishinaga			08/05/1999
<i>RL</i>	A94	6,372,356	04/16/2002	Thornton et al.			04/028/2000
<i>RL</i>	A95	6,399,970	06/04/2002	Kubo et al.			09/16/1997
<i>RL</i>	A96	6,407,406	06/18/2002	Tezuka			06/29/1999
<i>RL</i>	A97	6,425,951	07/30/2002	Chu et al.			08/06/1999
<i>RL</i>	A98	6,429,061	08/06/2002	Rim			07/26/2000
<i>RL</i>	A99	6,420,937	07/16/2002	Akatsuka et al.			06/14/2001
<i>RL</i>	A100	6,521,041	02/18/2003	Wu et al.			04/09/1999
<i>RL</i>	A101	6,555,839	04/29/2003	Fitzgerald			05/16/2001
<i>RL</i>	A102	6,583,015	06/24/2003	Fitzgerald et al.			08/06/2001
<i>RL</i>	A103	6,521,041	02/18/2003	Wu et al.			04/09/1999
<i>RL</i>	A104	2001/0003364	06/14/2001	Sugawara et al.			12/08/2000
<i>RL</i>	A105	2002/0043660	04/18/2002	Yamazaki et al.			06/25/2001
<i>RL</i>	A106	6,593,191	07/15/2003	Fitzgerald			05/16/2001
<i>RL</i>	A107	6,573,126	06/03/2003	Cheng et al.			08/10/2001
<i>RL</i>	A108	2002/0096717	07/25/2002	Chu et al.			01/25/2001
<i>RL</i>	A109	2002/0100942	08/01/2001	Fitzgerald et al.			06/19/2001
<i>RL</i>	A110	2002/0123167	09/05/2002	Fitzgerald			07/16/2001
<i>RL</i>	A111	2002/0123183	09/05/2002	Fitzgerald			07/16/2001
<i>RL</i>	A112	2002/0123197	09/05/2002	Fitzgerald et al.			06/19/2001
<i>RL</i>	A113	2002/0125471	09/12/2002	Fitzgerald et al.			12/04/2001
<i>RL</i>	A114	2002/0125497	09/12/2002	Fitzgerald			07/16/2001
<i>RL</i>	A115	6,603,156	08/05/2003	Rim			03/31/2001
<i>RL</i>	A116	2003/0003679	01/02/2003	Doyle et al.			06/29/2001

EXAMINER <i>Harvey Schatz</i>	DATE CONSIDERED <i>8/4/04</i>
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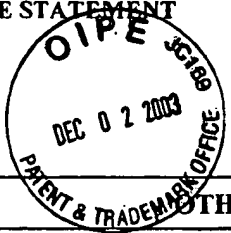
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 <b>FOREIGN PATENT DOCUMENTS</b>									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Al</i>	B1	41 01 167	07/23/1992	DE				NO	NO
<i>Al</i>	B2	0 587 520	03/16/1994	EP				NO	YES
<i>Al</i>	B3	0 683 522	11/22/1995	EP				NO	YES
<i>Al</i>	B4	0 828 296	03/11/1998	EP				NO	YES
<i>Al</i>	B5	0 829 908	03/18/1998	EP				NO	YES
<i>Al</i>	B6	0 838 858	04/29/1998	EP				NO	NO
<i>Al</i>	B7	1 020 900	07/19/2000	EP				NO	YES
<i>Al</i>	B8	1 174 928	01/23/2002	EP				NO	YES
<i>Al</i>	B9	2 342 777	04/19/2000	GB				YES	YES
<i>Al</i>	B10	10-270685	10/09/1998	JP				NO	YES
<i>Al</i>	B11	11-233744	08/27/1999	JP				NO	NO
<i>Al</i>	B12	2000-021783	08/31/2000	JP				NO	YES
<i>Al</i>	B13	2000-031491	01/28/2000	JP				NO	NO
<i>Al</i>	B14	2001-319935	11/16/2001	JP				NO	YES
<i>Al</i>	B15	2002-076334	03/15/2002	JP				NO	YES
<i>Al</i>	B16	2002-164520	06/07/2002	JP				NO	YES
<i>Al</i>	B17	2002-289533	10/04/2002	JP				NO	YES
<i>Al</i>	B18	4-307974	10/30/1992	JP				NO	NO
<i>Al</i>	B19	5-166724	07/02/1993	JP				NO	Abstract Only
<i>Al</i>	B20	6-177046	06/24/1994	JP				NO	Abstract Only
<i>Al</i>	B21	7-106446	04/21/1995	JP				NO	NO
<i>Al</i>	B22	7-240372	09/12/1995	JP				NO	Abstract Only
<i>Al</i>	B23	00/48239	08/17/2000	WO				NO	YES
<i>Al</i>	B24	00/54338	09/14/2000	WO				NO	YES

<b>EXAMINER</b> <i>Monica Schuyt</i>	<b>DATE CONSIDERED</b> <i>8/4/04</i>
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<b>FORM PTO - 1449</b>  <b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT</b>				<b>ATTY DOCKET NO.:</b> ASC-023DVC2  <b>APPLICANTS:</b> Fitzgerald  <b>SERIAL NO.:</b> 10/022,689  <b>FILING DATE:</b> December 17, 2001  <b>GROUP:</b> 2813					
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Re	B25	01/022482	03/29/2001	WO				NO	YES
Re	B26	01/54202	07/26/2001	WO				NO	YES
Re	B27	01/93338	12/06/2001	WO				NO	YES
Re	B28	01/99169	12/27/2001	WO				NO	YES
Re	B29	02/071488	09/12/2002	WO				NO	YES
Re	B30	02/071491	09/12/2002	WO				NO	YES
Re	B31	02/071495	09/12/2002	WO				NO	YES
Re	B32	02/082514	10/17/2002	WO				NO	YES
Re	B33	02/13262	02/14/2002	WO				NO	YES
Re	B34	02/15244	02/21/2002	WO				NO	YES
Re	B35	02/27783	04/04/2002	WO				NO	YES
Re	B36	02/47168	06/13/2002	WO				NO	YES
Re	B37	98/59365	12/30/1998	WO				NO	YES
Re	B38	99/53539	10/21/1999	WO				NO	YES
Re	B39	6-252046	11/19/1992	JP				NO	YES

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EXAMINER <i>hanna Selitz</i>	DATE CONSIDERED <i>8/4/04</i>
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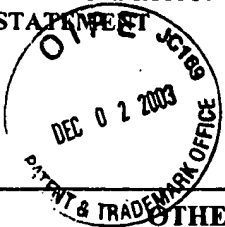
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		APPLICANTS: Fitzgerald
		SERIAL NO.: 10/022,689
		FILING DATE: December 17, 2001
		GROUP: 2813
OTHER ART, JOURNAL ARTICLES, ETC.		
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>pk</i>	C1	Armstrong et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," IEDM Technical Digest (1995 International Electron Devices Meeting) pp. 761-764.
<i>pk</i>	C2	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154.
<i>pk</i>	C3	Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997).
<i>pk</i>	C4	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," Modern Physics Letters B (2001) (abstract).
<i>pk</i>	C5	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," Proceedings of the 1999 12th IEEE International Conference on Micro Electro Mechanical Systems (MEMs) (January 17-21, 1999) pp. 205-210.
<i>pk</i>	C6	Bouillon et al., "Search for the optimal channel architecture for 0.18/0.12 $\mu$ m bulk CMOS Experimental study," IEEE, (1996) pp. 21.2.1-21.2.4.
<i>pk</i>	C7	Bruel et al., "@SMART CUT: A Promising New SOI Material Technology," Proceedings 1995 IEEE International SOI Conference (October 1995) pp. 178-179.
<i>pk</i>	C8	Bruel, "Silicon on Insulator Material Technology," Electronic Letters, Vol. 13, No. 14 (July 6, 1995) pp. 1201-1202.
<i>pk</i>	C9	Bufler et al., "Hole transport in strained Si <sub>1-x</sub> Ge <sub>x</sub> alloys on Si <sub>1-y</sub> Ge <sub>y</sub> substrates," Journal of Applied Physics, Vol. 84, No. 10 (November 15, 1998) pp. 5597-5602.
<i>pk</i>	C10	Burghartz et al., "Microwave Inductors and Capacitors in Standard Multilevel Interconnect Silicon Technology", IEEE Transactions on Microwave Theory and Techniques, Vol. 44, No. 1, January 1996, pp. 100-104.
<i>pk</i>	C11	Canaperi et al., "Preparation of a relaxed Si-Ge layer on an insulator in fabricating high-speed semiconductor devices with strained epitaxial films," International Business Machines Corporation, USA (2002) (abstract).
<i>pk</i>	C12	Carlin et al., "High Efficiency GaAs-on-Si Solar Cells with High Voc Using Graded GeSi Buffers," IEEE (2000) pp. 1006-1011
<i>pk</i>	C13	Chang et al., "Selective Etching of SiGe/Si Heterostructures," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 202-204.
<i>pk</i>	C14	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," IEEE Electron Device Letters, Vol. 22, No. 7 (July 2001) pp. 321-323.
<i>pk</i>	C15	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," Journal of Electronic Materials, Vol. 30, No. 12 (2001) pp. L37-L39.

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*Wanda Schultz*

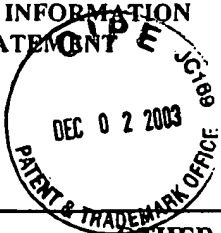


















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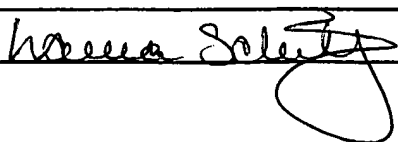
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<b>EXAM. INIT.</b>	<b>OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)</b>		
<i>He</i>	C16	Cullis et al., "Growth ripples upon strained SiGe epitaxial layers on Si and misfit dislocation interactions," Journal of Vacuum Science and Technology A, Vol. 12, No. 4 (July/August 1994) pp. 1924-1931.	
<i>He</i>	C17	Currie et al., "Carrier mobilities and process stability of strained S in- and p-MOSFETs on SiGe virtual substrates," J. Vac. Sci. Technol. B., Vol. 19, No. 6 (Nov/Dec 2001) pp. 2268-2279.	
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<i>He</i>	C19	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," Journal of Electronic Materials, Vol. 23, No. 6 (June 1994) pp. 493-496.	
<i>He</i>	C20	Fischetti et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys," J. Appl. Phys., Vol. 80, No. 4 (August 15, 1996) pp. 2234-2252.	
<i>He</i>	C21	Fischetti, "Long-range Coulomb interactions in small Si devices. Part II. Effective electron mobility in thin-oxide structures," Journal of Applied Physics, Vol. 89, No. 2 (January 15, 2001) pp. 1232-1250.	
<i>He</i>	C22	Fitzgerald et al., "Dislocation dynamics in relaxed graded composition semiconductors," Materials Science and Engineering B67, (1999) pp. 53-61.	
<i>He</i>	C23	Fitzgerald et al., "Relaxed GexSi1-x structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," AT&T Bell Laboratories, Murray Hill, NJ 07974 (1992) American Vacuum Society, pp. 1807-1819	
<i>He</i>	C24	Fitzgerald et al., "Totally Relaxed GexSi1-x Layers with Low Threading Dislocation Densities Grown on Si Substrates," Applied Physics Letters, Vol. 59, No. 7 (August 12, 1991) pp. 811-813.	
<i>He</i>	C25	Garone et al., "Silicon vapor phase epitaxial growth catalysis by the presence of germane," Applied Physics Letters, Vol. 56, No. 13 (March 26, 1990) pp. 1275-1277.	
<i>He</i>	C26	Gray and Meyer, "Analysis and Design of Analog Integrated Circuits", John Wiley & Sons, 1984, pp. 605-632.	
<i>He</i>	C27	Grützmacher et al., "Ge segregation in SiGe/Si heterostructures and its dependence on deposition technique and growth atmosphere," Applied Physics Letters, Vol. 63, No. 18 (November 1, 1993) pp. 2531-2533.	
<i>He</i>	C28	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," Thin Solid Films, Vol. 369, No. 1-2 (July 2000) pp. 148-151.	
<i>He</i>	C29	Hackbarth et al., "Strain relieved SiGe buffers for Si-based heterostructure field-effect transistors," Journal of Crystal Growth, Vol. 201/202 (1999) pp. 734-738.	
<i>He</i>	C30	Herzog et al., "SiGe-based FETs: buffer issues and device results," Thin Solid Films, Vol. 380 (2000) pp. 36-41.	
<i>He</i>	C31	Höck et al., "Carrier mobilities in modulation doped Si1-xGex heterostructures with respect to FET applications," Thin Solid Films, Vol. 336 (1998) pp. 141-144.	

<b>EXAMINER</b> <i>hanna Schubert</i>	<b>DATE CONSIDERED</b> <i>8/4/04</i>
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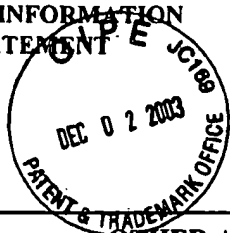















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	C32	Höck et al., "High hole mobility in Si <sub>0.17</sub> Ge <sub>0.83</sub> channel metal-oxide-semiconductor field-effect transistors grown by plasma-enhanced chemical vapor deposition," Applied Physics Letters, Volume 76, No. 26 (June 26, 2000) pp. 3920-3922.	
	C33	Höck et al., "High performance 0.25 μm p-type Ge/SiGe MODFETs," Electronics Letters, Vol. 34, No. 19 (September 17, 1998) pp. 1888-1889.	
	C34	Huang et al., "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," Applied Physics Letters, Vol. 76, No. 19 (May 8, 2000) pp. 2680-2682.	
	C35	Huang et al., "The Impact of Scaling Down to Deep Submicron on CMOS RF Circuits," IEEE Journal of Solid-State Circuits, Vol. 33, No. 7, July, 1998, pp. 1023-1036.	
	C36	IBM Technical Disclosure Bulletin, Vol. 35, No. 4B (September 1992), "2 Bit/Cell EEPROM Cell Using Band to Band Tunneling for Data Read-Out," pp. 136-140.	
	C37	IBM Technical Disclosure Bulletin, Volume 32, No. 8A, January 1990, "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates," pp. 330-331.	
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	C43	Kim et al., "A Fully Integrated 1.9-GHz CMOS Low-Noise Amplifier," IEEE Microwave and Guided Wave Letters, Vol. 8, No. 8, August 1998, pp. 293-295.	
	C44	Koester et al., "Extremely High Transconductance Ge/Si <sub>0.4</sub> Ge <sub>0.6</sub> p-MODFET's Grown by UHV-CVD," IEEE Electron Device Letters, Vol. 21, No. 3 (March 2000) pp. 110-112.	
	C45	König et al., "Design Rules for n-Type SiGe Hetero FETs," Solid State Electronics, Vol. 41, No. 10 (1997), pp. 1541-1547.	
	C46	König et al., "p-Type Ge-Channel MODFET's with High Transconductance Grown on Si Substrates," IEEE Electron Device Letters, Vol. 14, No. 4 (April 1993) pp. 205-207.	
	C47	König et al., "SiGe HBTs and HFETs," Solid-State Electronics, Vol. 38, No. 9 (1995) pp. 1595-1602.	
	C48	Kuznetsov et al., "Technology for high-performance n-channel SiGe modulation-doped field-effect transistors," J. Vac. Sci. Technol., B 13(6), pp. 2892-2896 (November/December 1995).	
	C49	Larson, "Integrated Circuit Technology Options for RFIC's □ Present Status and Future Directions," IEEE Journal of Solid-State Circuits, Vol. 33, No. 3, March 1998, pp. 387-399.	

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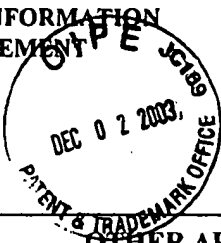




















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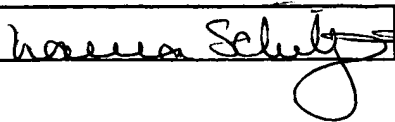
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
	C50	Lee and Wong, "CMOS RF Integrated Circuits at 5 GHz and Beyond", Proceedings of the IEEE, Vol. 88, No. 10, October 2000, pp. 1560-1571.
	C51	Lee et al., "Strained Ge channel p-type metal-oxide-semiconductor field-effect transistors grown on Si <sub>1-x</sub> Ge <sub>x</sub> /Si virtual substrates," Applied Physics Letters, Vol. 79, No. 20 (November 12, 2001) pp. 3344-3346.
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	C53	Leitz et al., "Channel Engineering of SiGe-Based Heterostructures for High Mobility MOSFETs," Mat. Res. Soc. Symp. Proc., Vol. 686 (2002) pp. A3.10.1-A3.10.6.
	C54	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," Journal of Applied Physics, Vol. 90, No. 6 (September 15, 2001) pp. 2730-2736.
	C55	Leitz et al., "Hole mobility enhancements in strained Si/Si <sub>1-y</sub> Ge <sub>y</sub> p-type metal-oxide-semiconductor field-effect transistors grown on relaxed Si <sub>1-x</sub> Ge <sub>x</sub> (x<y) virtual substrates," Applied Physics Letters, Vol. 79, No. 25 (December 17, 2001) pp. 4246-4248.
	C56	Li et al., "Design of high speed Si/SiGe heterojunction complementary metal-oxide-semiconductor field effect transistors with reduced short-channel effects," J. Vac. Sci. Technol., A Vol. 20 No.3 (May/June 2002) pp. 1030-1033.
	C57	Lu et al., "High Performance 0.1 $\mu$ m Gate-Length P-Type SiGe MODFET's and MOS-MODFET's," IEEE Transactions on Electron Devices, Vol. 47, No. 8, August 2000, pp. 1645-1652.
	C58	M. Kummer et al., "Low energy plasma enhanced chemical vapor deposition," Materials Science and Engineering B89 (2002) pp. 288-295.
	C59	Maiti et al., "Strained-Si heterostructure field effect transistors," Semicond. Sci. Technol., Vol. 13 (1998) pp. 1225-1246.
	C60	Mazara, "Silicon-On-Insulator by Wafer Bonding: A Review," Journal of the Electrochemical Society, No. 1 (January 1991) pp. 341-347.
	C61	Meyerson et al., "Cooperative Growth Phenomena in Silicon/Germanium Low-Temperature Epitaxy," Applied Physics Letters, Vol. 53, No. 25 (December 19, 1988) pp. 2555-2557.
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	C64	Mizuno et al., "High Performance Strained-Si p-MOSFETs on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," IEEE IDEM Technical Digest, (1999 International Electron Device Meeting) pp. 934-936.

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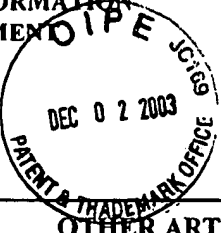
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	C65	Nayak et al., "High-Mobility Strained-Si PMOSFET's"; IEEE Transactions on Electron Devices, Vol. 43, No. 10, October 1996, pp. 1709-1716.	
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	C67	Papananos, "Radio-Frequency Microelectronic Circuits for Telecommunication Applications", Kluwer Academic Publishers, 1999, pp. 115-117, 188-193.	
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	C71	Reinking et al., "Fabrication of high-mobility Ge p-channel MOSFETs on Si substrates," Electronics Letters, Vol. 35, No. 6 (March 18, 1999) pp. 503-504.	
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	C73	Rim et al., "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's"; IEEE Transactions on Electron Devices, Vol. 47, No. 7, July 2000, pp. 1406-1415.	
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	C77	Schäffler, "High-Mobility Si and Ge Structures," Semiconductor Science and Technology, Vol. 12 (1997) pp. 1515-1549.	
	C78	Sugimoto and Ueno, "A 2 V, 500 MHz and 3 V, 920 MHz Low-Power Current-Mode 0.6 $\mu$ m CMOS VCO Circuit", IEICE Trans. Electron., Vol. E82-C, No. 7, July 1999, pp. 1327-1329.	
	C79	Ternent et al., "Metal Gate Strained Silicon MOSFETs for Microwave Integrated Circuits", IEEE October 2000, pp. 38-43.	
	C80	Tweet et al., "Factors determining the composition of strained GeSi layers grown with disilane and germane," Applied Physics Letters, Vol. 65, No. 20 (November 14, 1994) pp. 2579-2581.	
	C81	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," Semicon. Sci. Technol. (1997) (abstract).	
	C82	Welser et al., "Electron Mobility Enhancement in Strained-Si N-Type Metal-Oxide-Semiconductor Field-Effect Transistors," IEEE Electron Device Letters, Vol. 15, No. 3 (March 1994) pp. 100-102.	

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<i>He</i>	C83	Welser, "The Application of Strained Silicon/Relaxed Silicon Germanium Heterostructures to Metal-Oxide-Semiconductor Field-Effect Transistors," PhD Thesis, Stanford University, 1994, pp. 1-205.
<i>He</i>	C84	Welser et al., "NMOS and PMOS Transistors Fabricated in Strained Silicon/Relaxed Silicon-Germanium Structures," IEEE IDEM Technical Digest (1992 International Electron Devices Meeting) pp. 1000-1002.
<i>He</i>	C85	Welser et al., "Evidence of Real-Space Hot-Electron Transfer in High Mobility, Strained-Si Multilayer MOSFETs," IEEE IDEM Technical Digest (1993 International Electron Devices Meeting) pp. 545-548.
<i>He</i>	C86	Wolf and Tauber, Silicon Processing for the VLSI Era, Vol. 1: Process Technology, Lattice Press, Sunset Beach, CA, pp. 384-386 (1986).
<i>He</i>	C87	Xie et al., "Semiconductor Surface Roughness: Dependence on Sign and Magnitude of Bulk Strain," The Physical Review Letters, Vol. 73, No. 22 (November 28, 1994) pp. 3006-3009.
<i>He</i>	C88	Xie et al., "Very high mobility two-dimensional hole gas in Si/ Ge <sub>x</sub> Si <sub>1-x</sub> /Ge structures grown by molecular beam epitaxy," Appl. Phys. Lett., Vol. 63, No. 16 (October 18, 1993) pp. 2263-2264.
<i>He</i>	C89	Xie, "SiGe Field effect transistors," Materials Science and Engineering, Vol. 25 (1999) pp. 89-121.
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